

Supporting information

Near-infrared polymer light emitting diodes based on an inverted device structure

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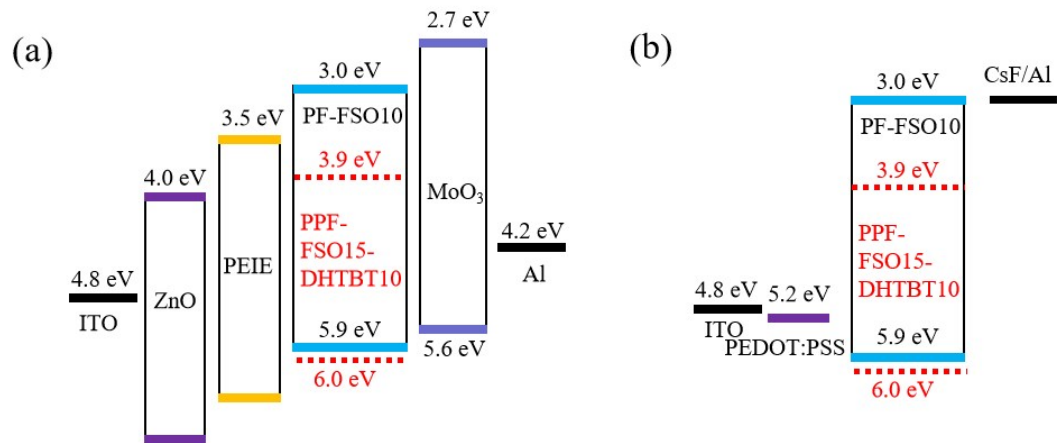


Fig. S1 Energy level diagram of IPLED (a) and CPLED (b).

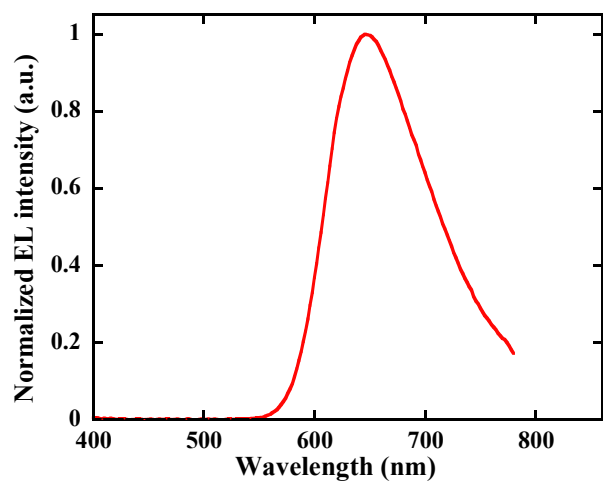


Fig. S2 EL spectrum of PPF-FSO15-DHTBT10 for CPLED device.

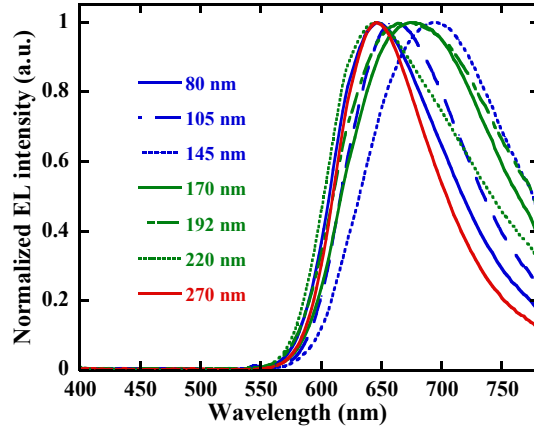


Fig. S3 EL spectra based on different thickness of emissive layer (PPF-FSO15-DHTBT10) for IPLED.

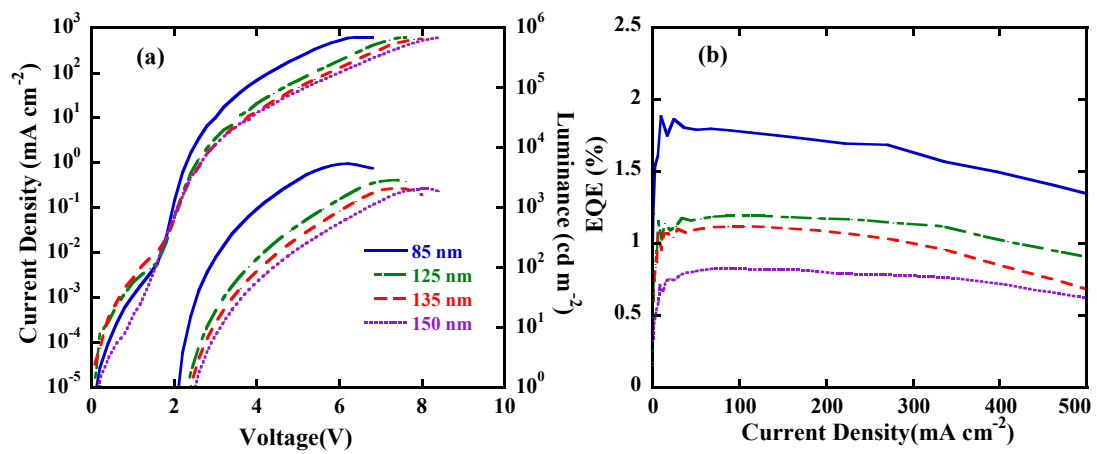


Fig. S4 J-V-L(a) and EQE-J(b) of different thickness of MEH-PPV annealing at 100 °C.

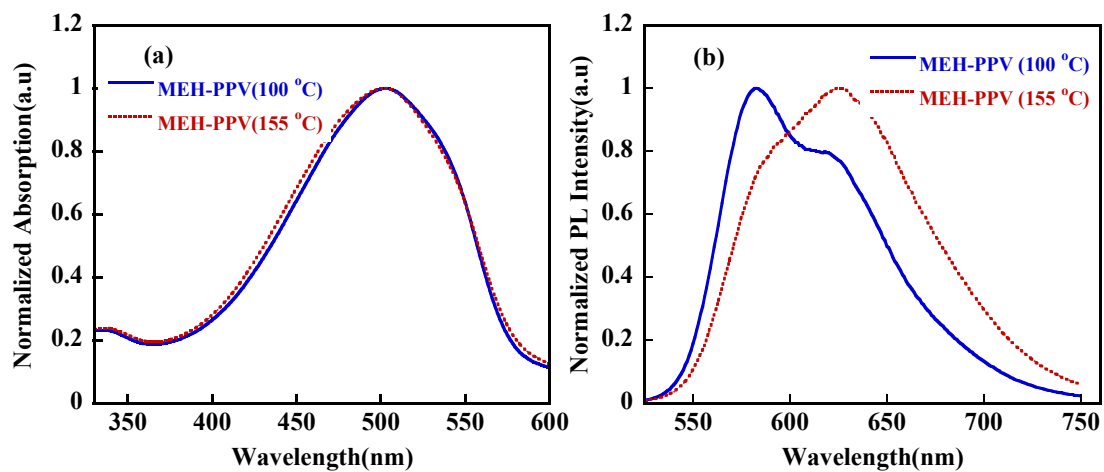


Fig. S5 UV-vis absorption spectra (a) and PL spectra (b) of MEH-PPV film based on different annealing temperature.

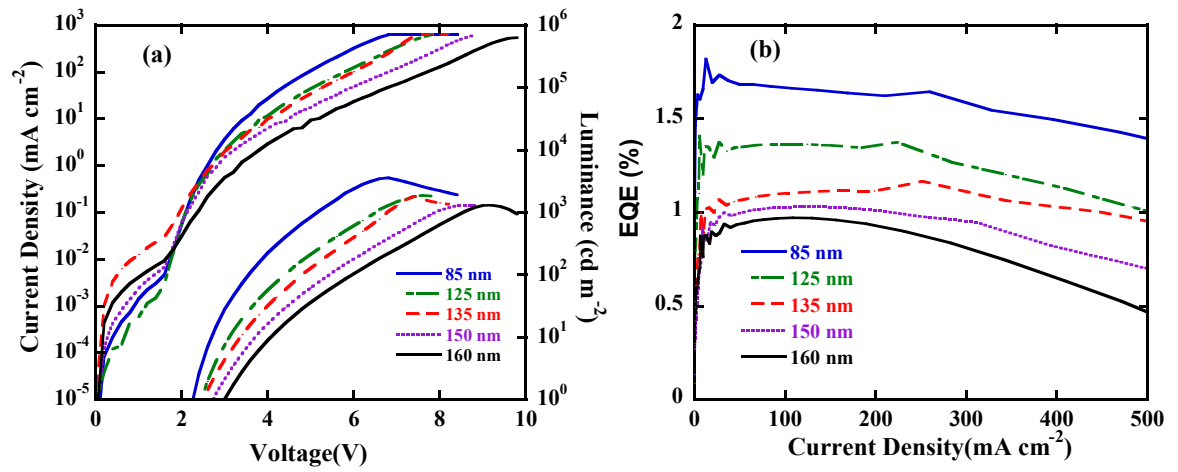


Fig. S6 J-V-L(a) and EQE-J(b) of different thickness of MEH-PPV annealing at 155 °C.